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SEMICONDUCTOR®

# FGA180N33AT 330V, 180A PDP Trench IGBT

## Features

- High Current Capability
- Low saturation voltage: V<sub>CE(sat)</sub> =1.03V @ I<sub>C</sub> = 40A
- High input impedance
- · RoHS compliant

# Applications

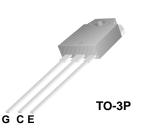
PDP SYSTEM

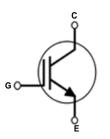


# **General Description**

Using Novel Trench IGBT Technology, Fairchild's new series of trench IGBTs offer the optimum performance for PDP applications where low conduction and switching losses are essential.

April 2008





# **Absolute Maximum Ratings**

Symbol	Description		Ratings	Units
V <sub>CES</sub>	Collector to Emitter Voltage		330	V
V <sub>GES</sub>	Gate to Emitter Voltage		$\pm 30$	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25 <sup>o</sup> C	180	A
I <sub>C pulse (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	450	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25 <sup>o</sup> C	390	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	156	W
TJ	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C

Notes:

1: Repetitive test, pulse width = 100usec, Duty = 0.1

\* I<sub>C\_</sub>pulse limited by max Tj

# **Thermal Characteristics**

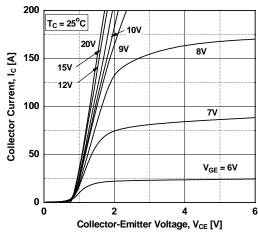
Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.32	°C/W
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

				Packaging				Qty per
Device Marking		Device	Package	Туре	Qty pe	er Tube	Box	
FGA180N33AT FGA180N33ATTU		TO-3P	TO-3P Tube		30ea		-	
Electric	al Cha	racteristics of th	ne IGBT T <sub>c = 2</sub>	5°C unless otherwise noted				
Symbol		Parameter	Test	Conditions	Min.	Тур.	Max.	Units
Off Charac	teristics							
BV <sub>CES</sub>	Collector	to Emitter Breakdown Vo	Itage V <sub>GE</sub> = 0V, I <sub>C</sub>	e = 250μA	330	-	-	V
ICES		Cut-Off Current	V <sub>CE</sub> = V <sub>CES</sub>		-	-	250	μA
I <sub>GES</sub>	G-E Leak	age Current	V <sub>GE</sub> = V <sub>GES</sub>		-	-	±400	nA
On Charac	toristics					1		1
V <sub>GE(th)</sub>		G-E Threshold Voltage		$I_{\rm C}$ = 250uA, $V_{\rm CE}$ = $V_{\rm GE}$		4.0	5.5	V
	Collector to Emitter Saturation Voltage		I <sub>C</sub> = 40A, V <sub>G</sub>		-	1.1	1.4	V
			I <sub>C</sub> = 180A, V	<sub>GE</sub> = 15V,	-	1.68	-	V
			I <sub>C</sub> = 180A, V T <sub>C</sub> = 125°C	<sub>GE</sub> = 15V	-	1.89	_	V
Dynamic C	haractoris	tion						1
C <sub>ies</sub>	Input Cap			V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz		3880	-	pF
C <sub>oes</sub>	Output Ca	apacitance				305	-	pF
C <sub>res</sub>	Reverse	Transfer Capacitance	f = 1MHz			180	-	pF
	Character							I
Switching t <sub>d(on)</sub>		Delay Time			-	27	-	ns
t <sub>r</sub>	Rise Time		$V_{\rm CC} = 200 V_{\rm cc}$	I <sub>C</sub> = 40A,	-	80	-	ns
t <sub>d(off)</sub>	Turn-Off I	Delay Time	$R_G = 5\Omega, V_G$	<sub>GE</sub> = 15V, ad, T <sub>C</sub> = 25 <sup>o</sup> C	-	108	-	ns
t <sub>f</sub>	Fall Time			uu, 10 - 20 0	-	180	240	ns
t <sub>d(on)</sub>	Turn-On I	Delay Time			-	26	-	ns
t <sub>r</sub>	Rise Time	9	$V_{\rm CC} = 200V_{\rm CC}$	$I_{\rm C} = 40$ A,	-	75	-	ns
t <sub>d(off)</sub>	Turn-Off I	Delay Time	R <sub>G</sub> = 5Ω, V <sub>G</sub> Resistive Lo	<sub>GE</sub> = 15V, ad, T <sub>C</sub> = 125°C	-	112	-	ns
t <sub>f</sub>	Fall Time			J	-	250	300	ns
Qg	Total Gate	e Charge			-	169	-	nC
Q <sub>ge</sub>	Gate to E	mitter Charge	$V_{CE} = 200V,$	I <sub>C</sub> = 40A,	-	22	-	nC
Q <sub>gc</sub>	Gate to C	ollector Charge	vGE = 15V	V <sub>GE</sub> = 15V		69	-	nC

# FGA180N33AT 330V, 180A PDP Trench IGBT

## **Typical Performance Characteristics**

**Figure 1. Typical Output Characteristics** 





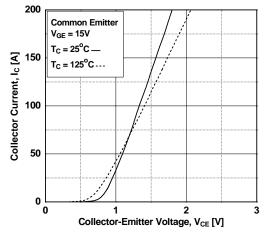
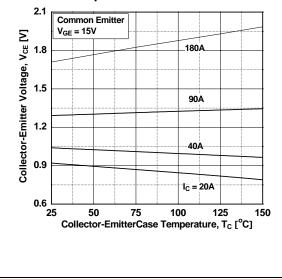
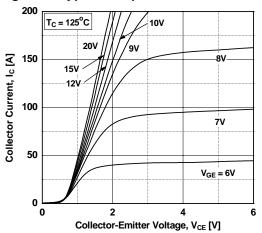


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level



**Figure 2. Typical Output Characteristics** 



**Figure 4. Transfer Characteristics** 

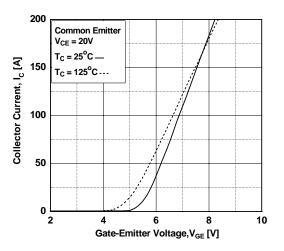
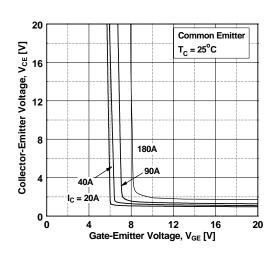


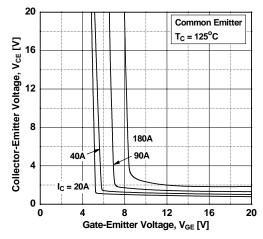
Figure 6. Saturation Voltage vs. V<sub>GE</sub>



# FGA180N33AT 330V, 180A PDP Trench IGBT

## **Typical Performance Characteristics**

### Figure 7. Saturation Voltage vs. V<sub>GE</sub>



**Figure 9. Gate charge Characteristics** 

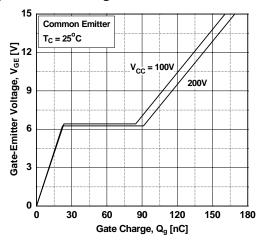
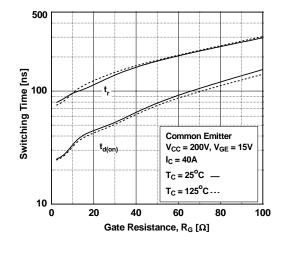
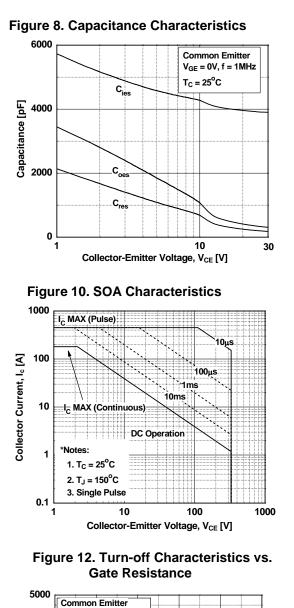
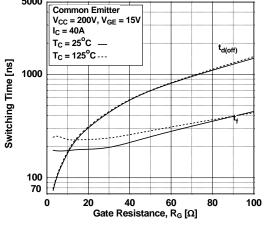


Figure 11. Turn-on Characteristics vs. Gate Resistance







### FGA180N33AT Rev. A

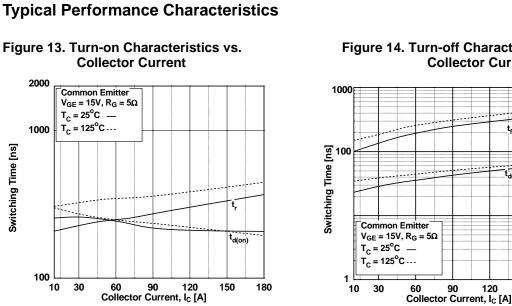
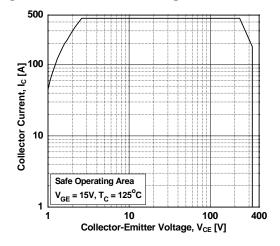
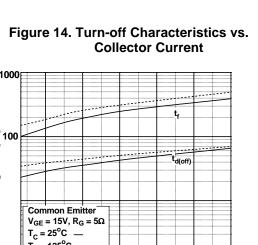


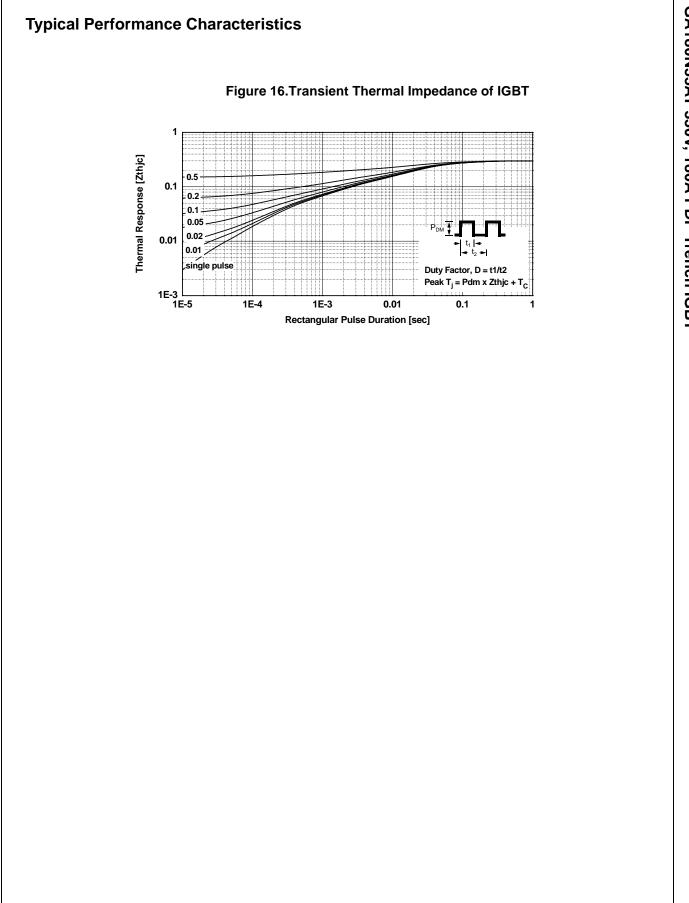
Figure 15. Turn off Switching SOA Characteristics

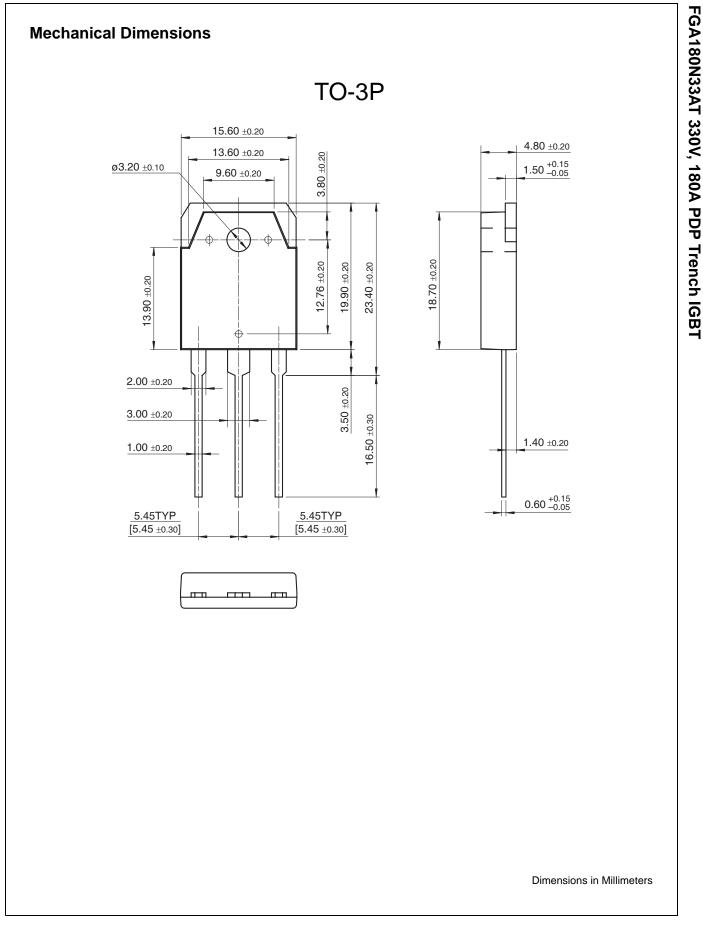




150

180





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